



# STL150N3LLH5

N-channel 30 V - 0.0014  $\Omega$  - 35 A - PowerFLAT™ (6x5)  
STripFET™ V Power MOSFET

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STL150N3LLH5	30 V	<0.00175 $\Omega$	35 A <sup>(1)</sup>

1. The value is rated according R<sub>thj-pcb</sub>

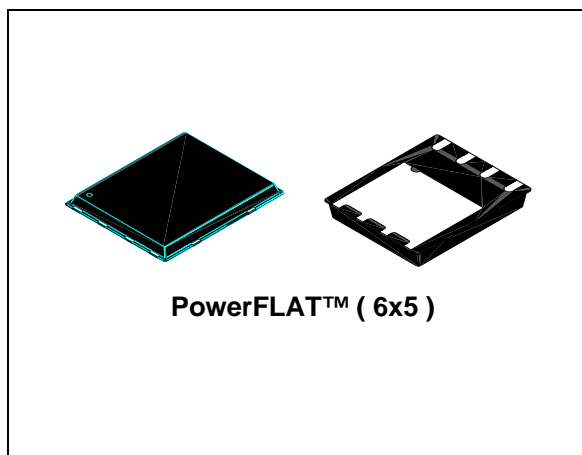
- R<sub>DS(on)</sub> \* Q<sub>g</sub> industry benchmark
- Extremely low on-resistance R<sub>DS(on)</sub>
- High avalanche ruggedness
- Low gate drive power losses

## Application

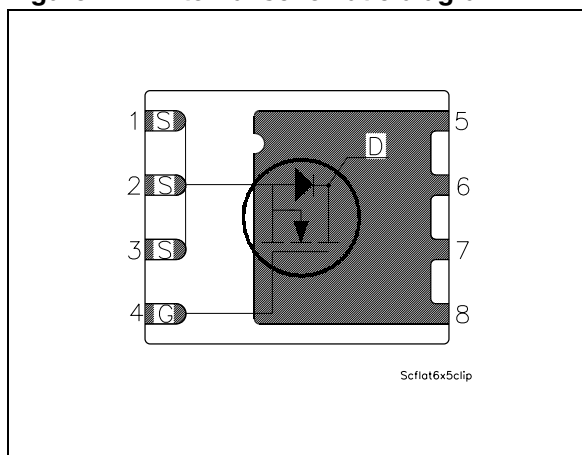
- Switching applications

## Description

This product utilizes the 5<sup>th</sup> generation of design rules of ST's proprietary STripFET™ technology. The lowest available R<sub>DS(on)</sub>\*Q<sub>g</sub>, in this chip scale package, makes this device suitable for the most demanding DC-DC converter applications, where high power density is to be achieved.



**Figure 1. Internal schematic diagram**



**Table 1. Device summary**

Order code	Marking	Package	Packaging
STL150N3LLH5	150N3LLH5	PowerFLAT™ (6x5)	Tape and reel

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	30	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	150	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	94	A
$I_D^{(2)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	35	A
$I_D^{(3)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	21.8	A
$I_{DM}^{(3)}$	Drain current (pulsed)	140	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	80	W
$P_{TOT}^{(3)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	4	W
	Derating factor	0.03	W/ $^\circ\text{C}$
$T_J$	Operating junction temperature	-55 to 150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		

1. The value is rated according  $R_{thj-c}$
2. The value is rated according  $R_{thj-pcb}$
3. Pulse width limited by safe operating area

**Table 3. Thermal resistance**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case (drain) (steady state)	1.56	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-ambient	31.3	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of 1inch<sup>2</sup>, 2oz Cu,  $t < 10\text{ sec}$

**Table 4. Avalanche data**

Symbol	Parameter	Value	Unit
$I_{AV}$	Not-repetitive avalanche current, (pulse width limited by $T_J \text{ Max}$ )	17	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$ , $I_D = I_{AV}$ , $V_{DD} = 24\text{ V}$ )	300	mJ

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = 0$	30			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating}$ , $V_{DS} = \text{Max rating @ } 125\text{ °C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	1			V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 17.5\text{ A}$ $V_{GS} = 4.5\text{ V}$ , $I_D = 17.5\text{ A}$		0.0014 0.0019	0.00175 0.0024	$\Omega$ $\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$		5800		pF
$C_{oss}$	Output capacitance			1147		pF
$C_{rss}$	Reverse transfer capacitance			127		pF
$Q_g$	Total gate charge	$V_{DD} = 15\text{ V}$ , $I_D = 35\text{ A}$ $V_{GS} = 4.5\text{ V}$ (see Figure 14)		40		nC
$Q_{gs}$	Gate-source charge			13.4		nC
$Q_{gd}$	Gate-drain charge			14.9		nC
$R_G$	Gate input resistance	$f = 1\text{ MHz}$ Gate DC Bias = 0 Test signal level = 20 mV open drain		1.1		$\Omega$

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=15\text{ V}$ , $I_D=17.5\text{ A}$ , $R_G=4.7\ \Omega$ , $V_{GS}=10\text{ V}$ (see Figure 13)		17.2		ns
$t_r$	Rise time			30.8		ns
$t_{d(off)}$	Turn-off delay time			65.8		ns
$t_f$	Fall time			47.8		ns

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$I_{SD}$	Source-drain current				35	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				140	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=35\text{ A}$ , $V_{GS}=0$			1.1	V
$t_{rr}$	Reverse recovery time	$I_{SD}=35\text{ A}$ , $di/dt=100\text{ A}/\mu\text{s}$ , $V_{DD}=25\text{ V}$		43.8		ns
$Q_{rr}$	Reverse recovery charge			46		nC
$I_{RRM}$	Reverse recovery current			2.1		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration=300 $\mu\text{s}$ , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

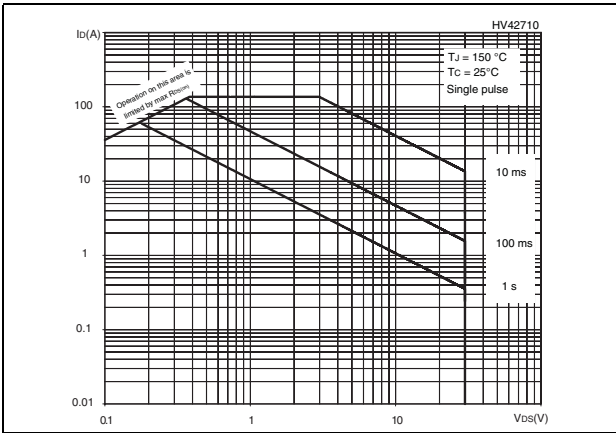


Figure 3. Thermal impedance

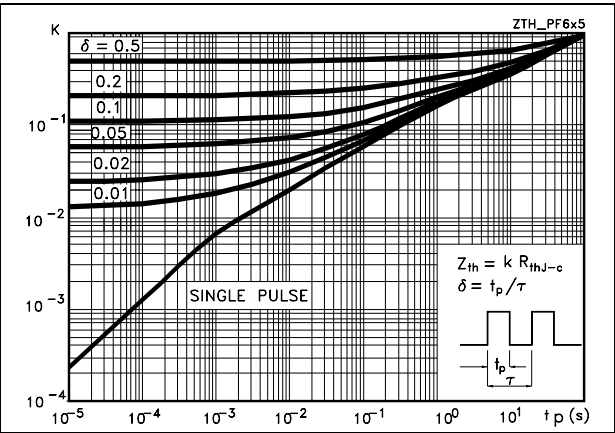


Figure 4. Output characteristics

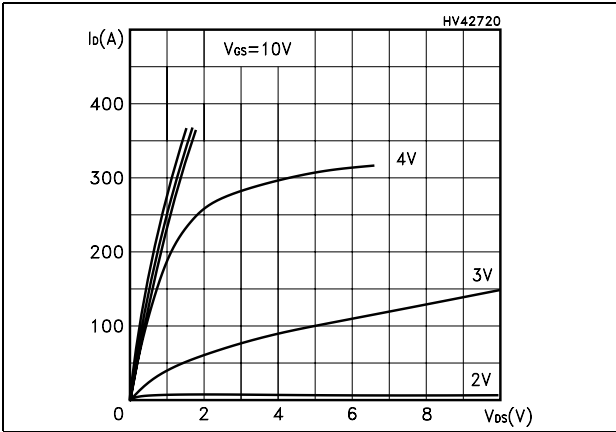


Figure 5. Transfer characteristics

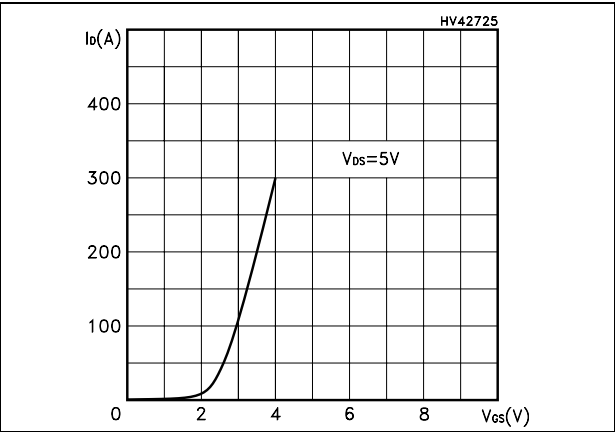


Figure 6. Normalized  $B_{VDS}$  vs temperature

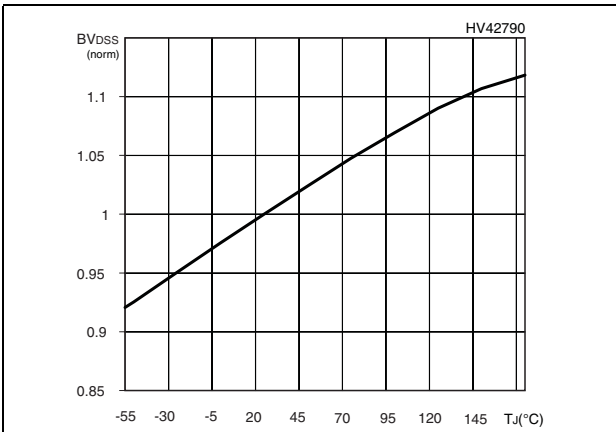


Figure 7. Static drain-source on resistance

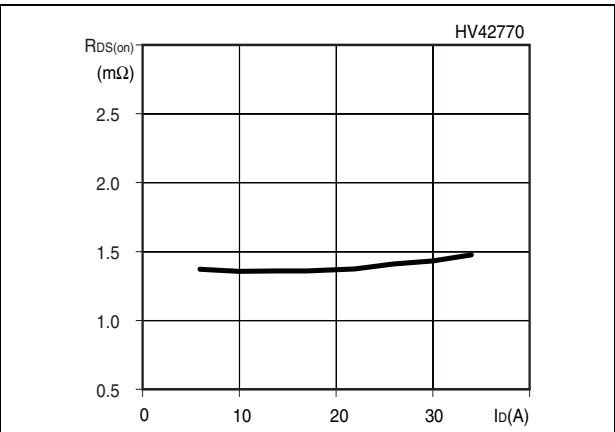


Figure 8. Gate charge vs gate-source voltage    Figure 9. Capacitance variations

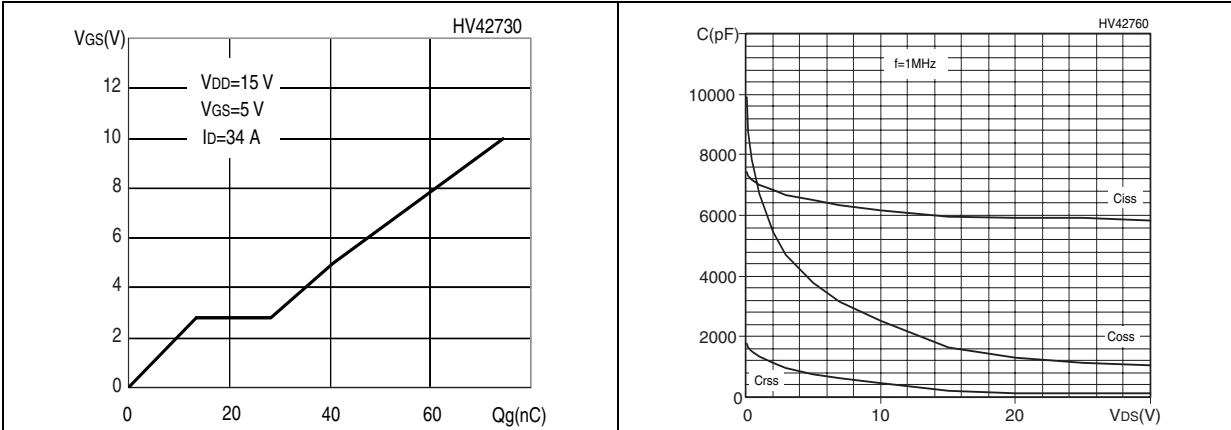


Figure 10. Normalized gate threshold voltage vs temperature    Figure 11. Normalized on resistance vs temperature

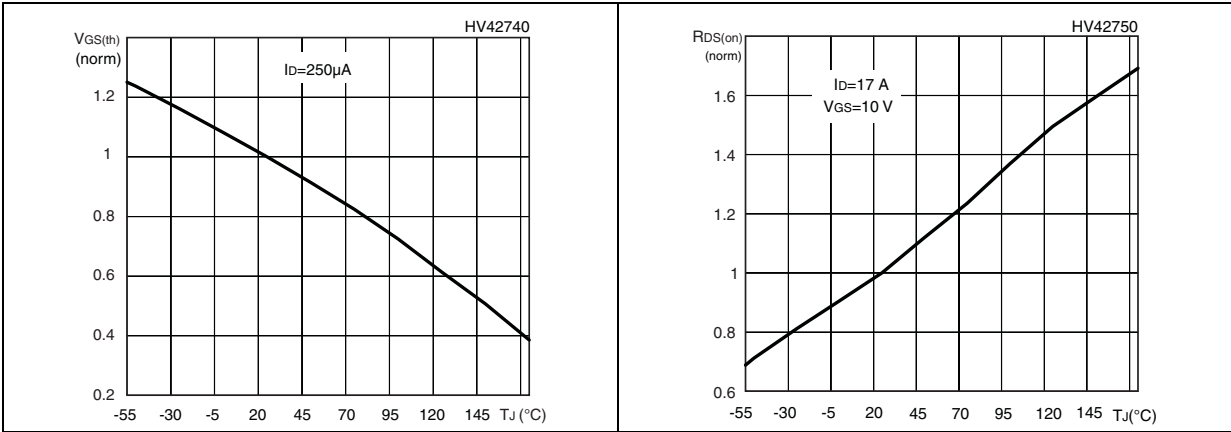
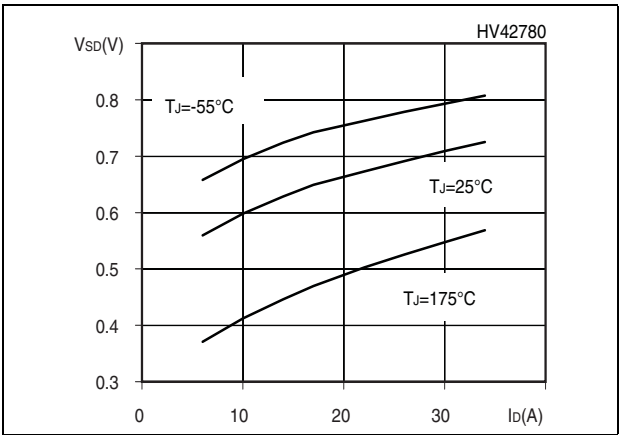
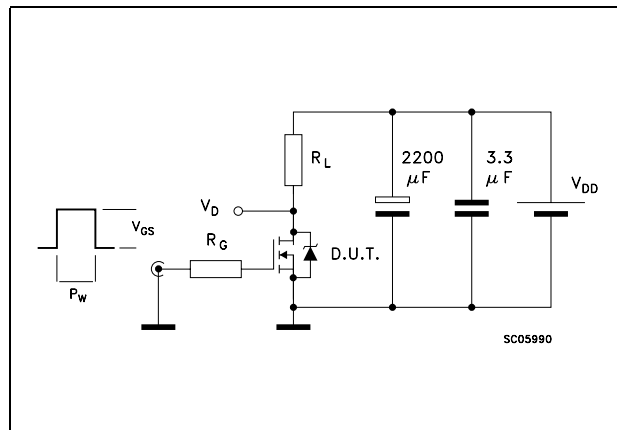


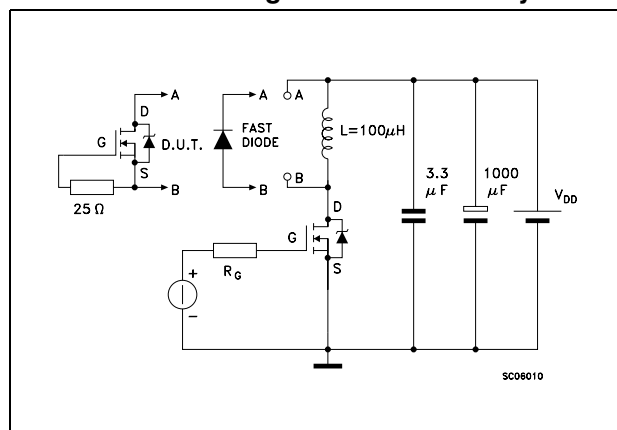
Figure 12. Source-drain diode forward characteristics



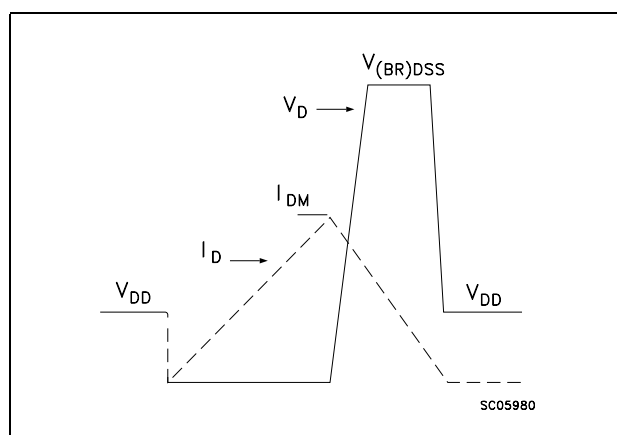
**Figure 13. Switching times test circuit for resistive load**



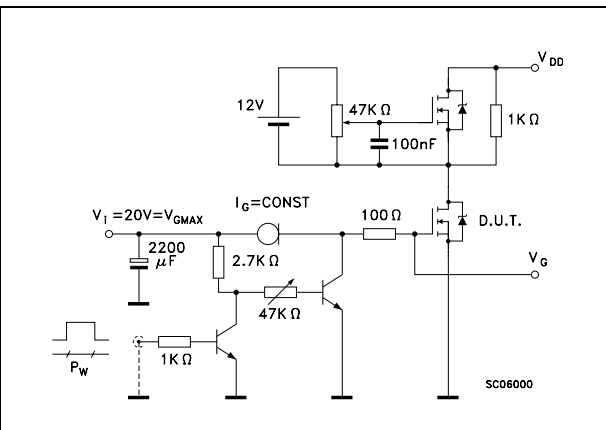
**Figure 15. Test circuit for inductive load switching and diode recovery times**



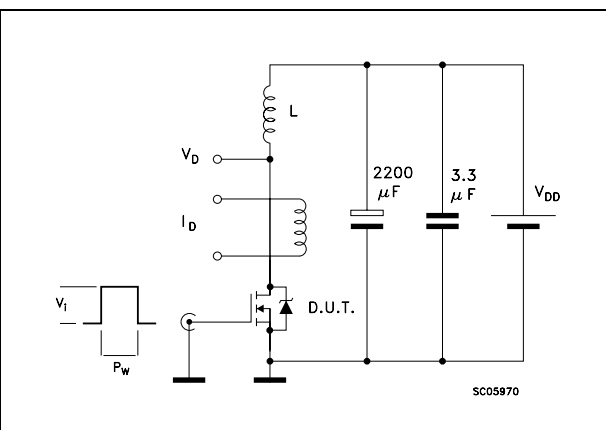
**Figure 17. Unclamped inductive waveform**



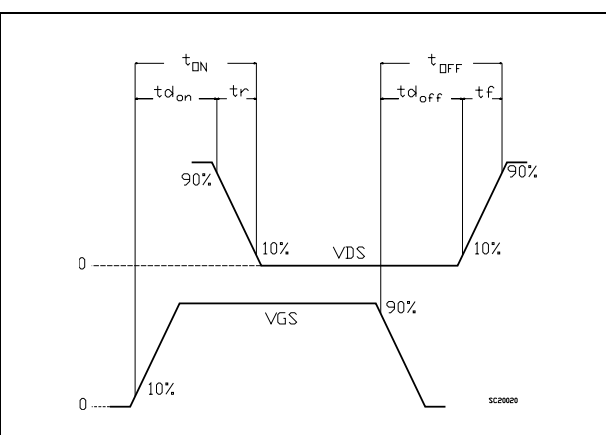
**Figure 14. Gate charge test circuit**



**Figure 16. Unclamped inductive load test circuit**



**Figure 18. Switching time waveform**



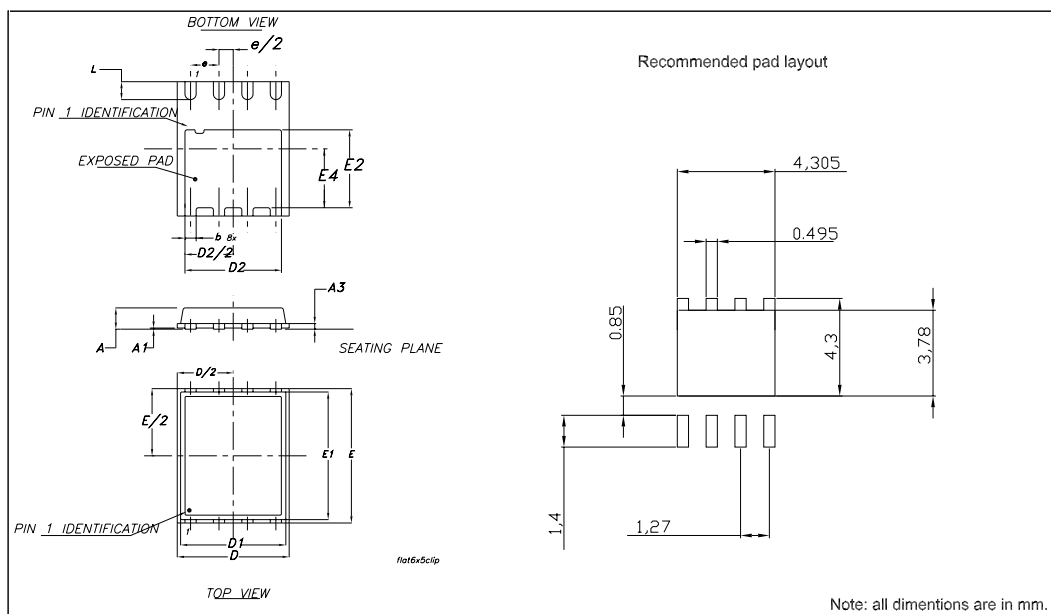


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

## PowerFLAT™(6x5) mechanical data

DIM.	mm.			inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.80	0.83	0.93	0.031	0.32	0.036
A1		0.02	0.05		0.0007	0.0019
A3		0.20			0.007	
b	0.35	0.40	0.47	0.013	0.015	0.018
D		5.00			0.196	
D1		4.75			0.187	
D2	4.15	4.20	4.25	0.163	0.165	0.167
E		6.00			0.236	
E1		5.75			0.226	
E2	3.43	3.48	3.53	0.135	0.137	0.139
E4	2.58	2.63	2.68		0.103	0.105
e		1.27			0.050	
L	0.70	0.80	0.90	0.027	0.031	0.035



## 5 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
22-Oct-2007	1	First release
01-Apr-2008	2	Document status promoted from preliminary data to datasheet

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